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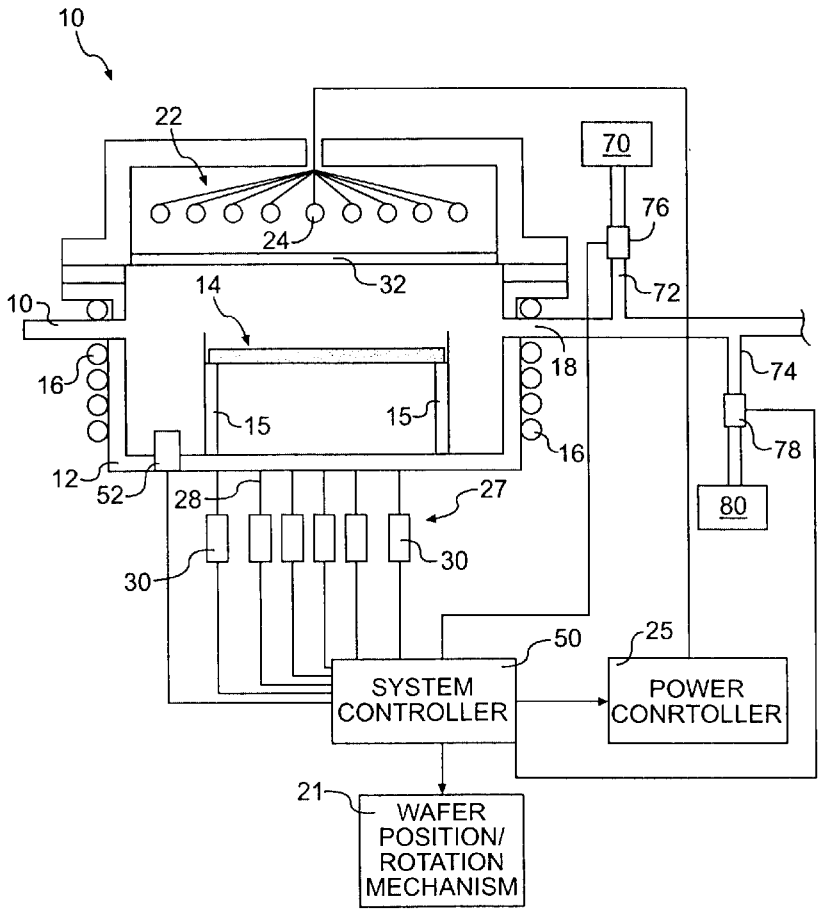
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(54) Title: METHOD OF FORMING DIELECTRIC FILMS



(57) Abstract: A method for depositing a high-k dielelectric coating onto a substrate, such as a semiconductor wafer, is provided. In one embodiment, the process is directed to forming a nitride layer on a substrate. In an alternative embodiment, the present invention is directed to forming a metal oxide or silicate on a semiconductor wafer. When forming a metal oxide or silicate, a passivation layer is first deposited onto the substrate.

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